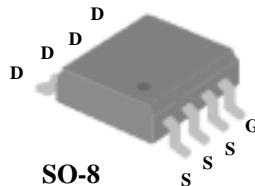




**Advanced Power
Electronics Corp.**

**N-CHANNEL ENHANCEMENT MODI
POWER MOSFET**

- ▼ Low On-Resistance
- ▼ Fast Switching
- ▼ Simple Drive Requirement

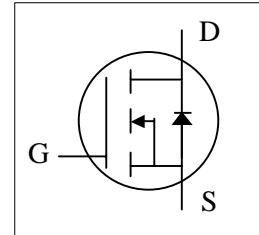


BV_{DSS}	25V
$R_{DS(ON)}$	8.5mΩ
I_D	13A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	25	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current ³	13	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current ³	10	A
I_{DM}	Pulsed Drain Current ¹	50	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
$R_{thj-amb}$	Thermal Resistance Junction-ambient ³	Max. 50	°C/W

**AP4880M****Electrical Characteristics@T_j=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	25	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.037	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =13A	-	-	8.5	mΩ
		V _{GS} =4.5V, I _D =10A	-	-	15	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _f	Forward Transconductance	V _{DS} =15V, I _D =10A	-	20	-	S
I _{DSS}	Drain-Source Leakage Current (T=25°C)	V _{DS} =25V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T=70°C)	V _{DS} =20V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ± 20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =13A	-	22.5	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} =15V	-	3.3	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =5V	-	15.4	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =15V	-	9	-	ns
t _r	Rise Time	I _D =1A	-	16	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =6.2Ω, V _{GS} =10V	-	25	-	ns
t _f	Fall Time	R _D =15Ω	-	50	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	813	-	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	516	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	224	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I _s	Continuous Source Current (Body Diode)	V _D =V _G =0V , V _S =1.3V	-	-	1.92	A
V _{SD}	Forward On Voltage ²	T _j =25°C, I _s =2.3A, V _{GS} =0V	-	-	1.3	V

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mounted on 1 in² copper pad of FR4 board ; 125 °C/W when mounted on Min. copper pad.

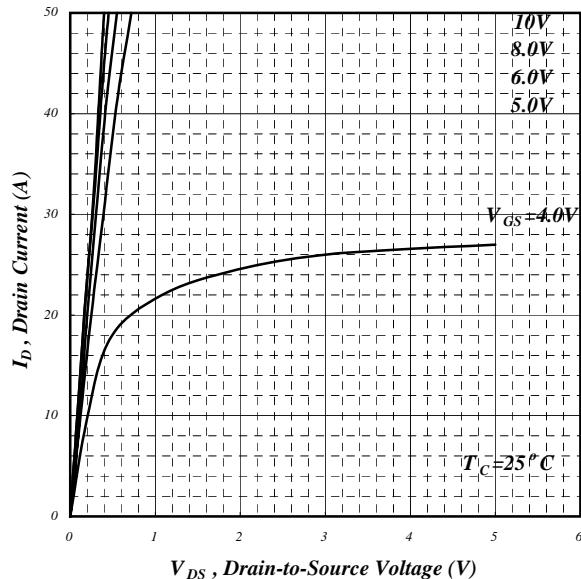


Fig 1. Typical Output Characteristics

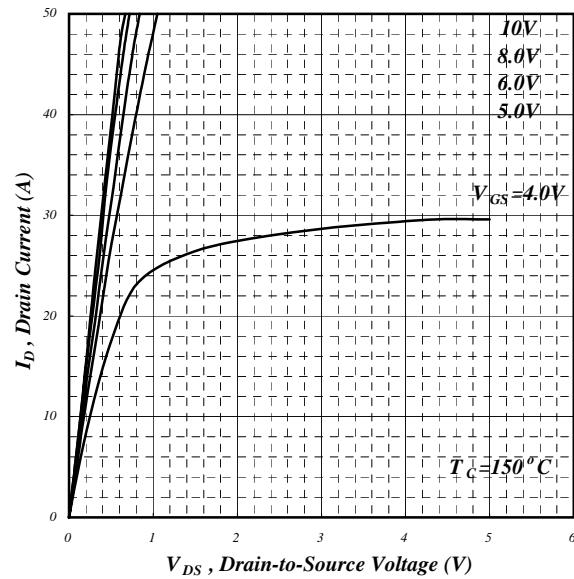


Fig 2. Typical Output Characteristics

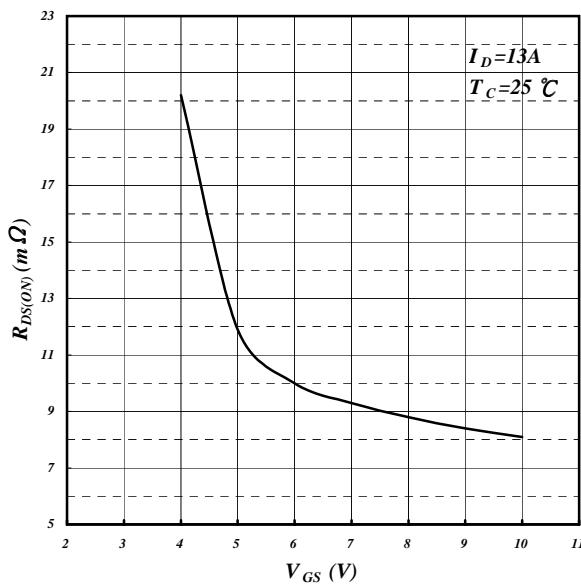


Fig 3. On-Resistance v.s. Gate Voltage

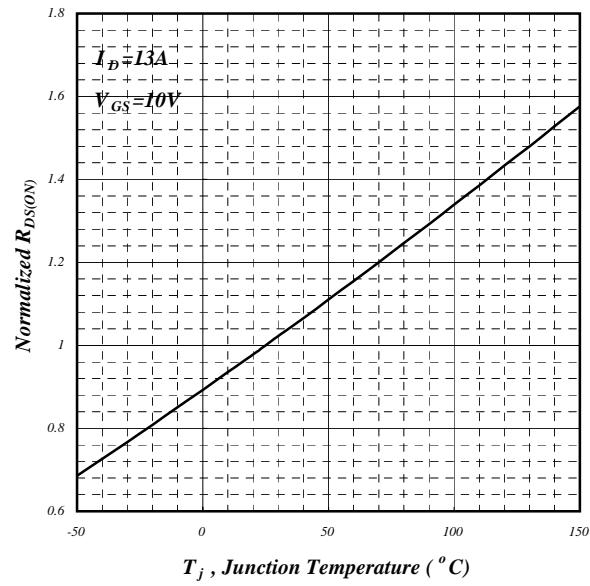
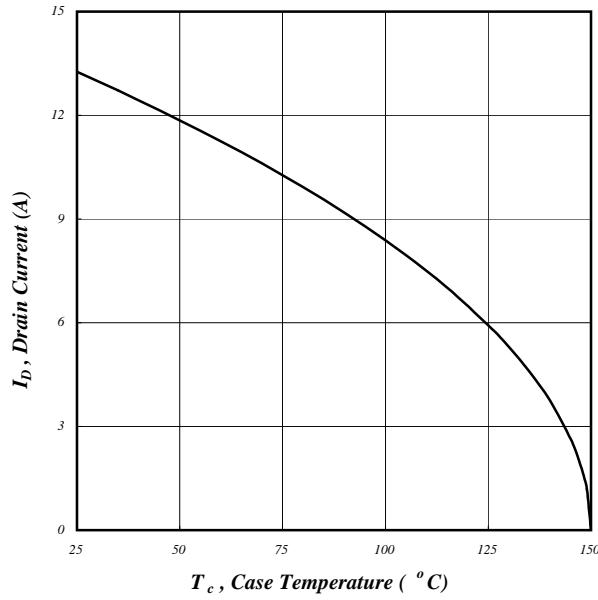


Fig 4. Normalized On-Resistance v.s. Junction Temperature



**Fig 5. Maximum Drain Current v.s.
Case Temperature**

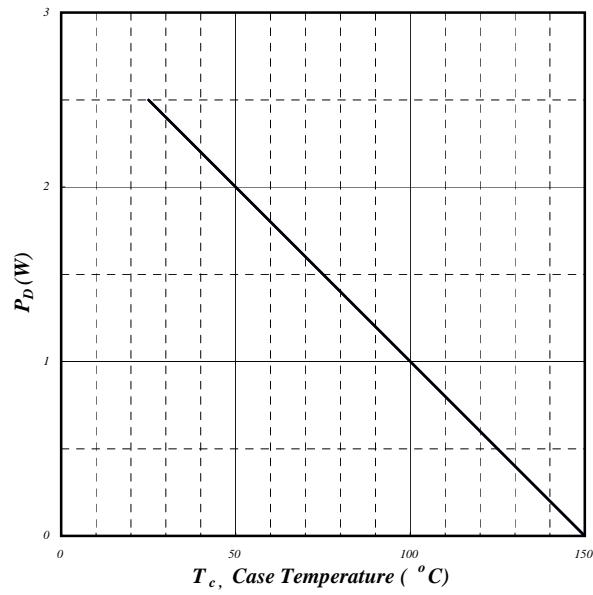


Fig 6. Typical Power Dissipation

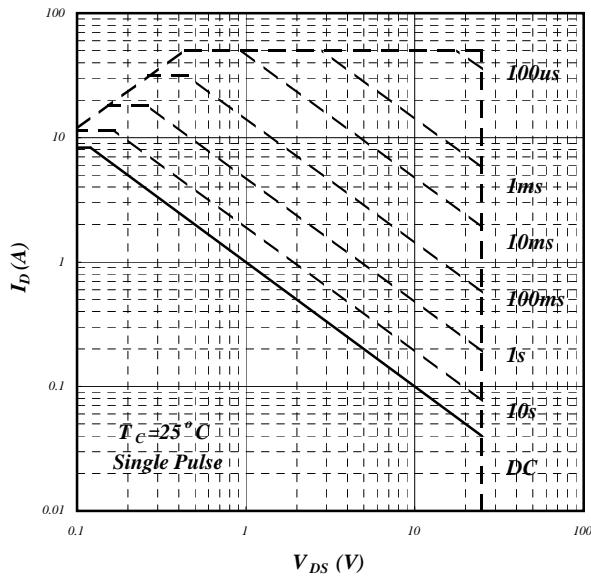


Fig 7. Maximum Safe Operating Area

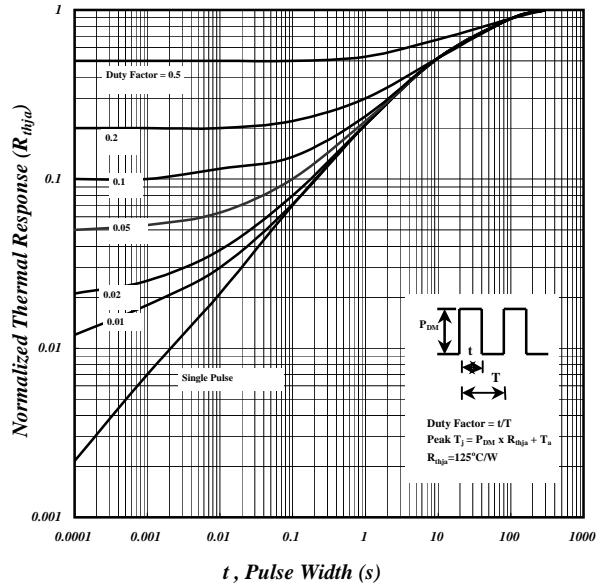


Fig 8. Effective Transient Thermal Impedance



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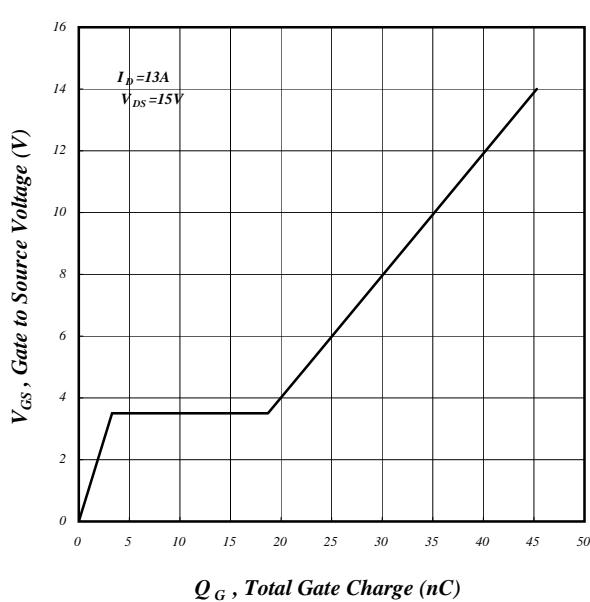


Fig 9. Gate Charge Characteristics

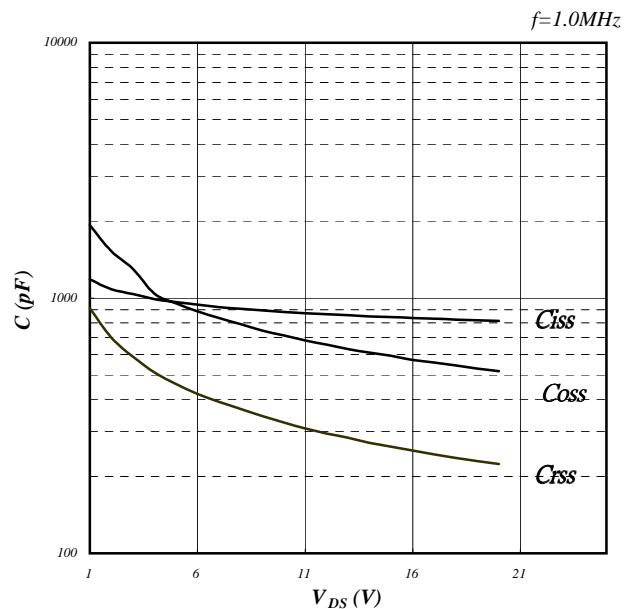


Fig 10. Typical Capacitance Characteristics

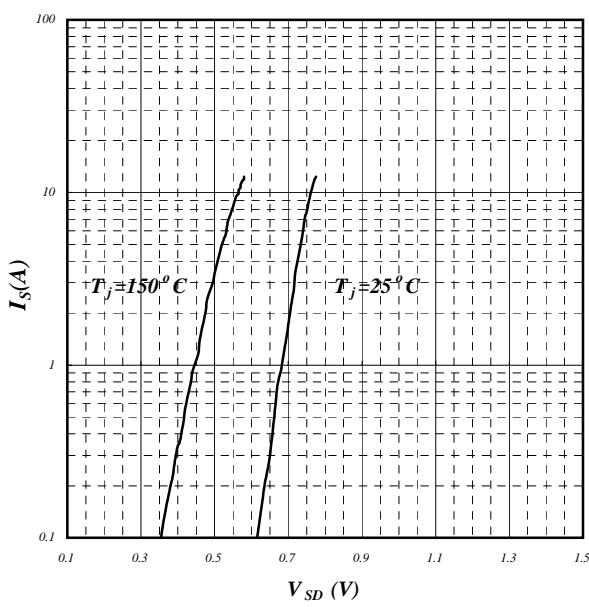


Fig 11. Forward Characteristic of Reverse Diode

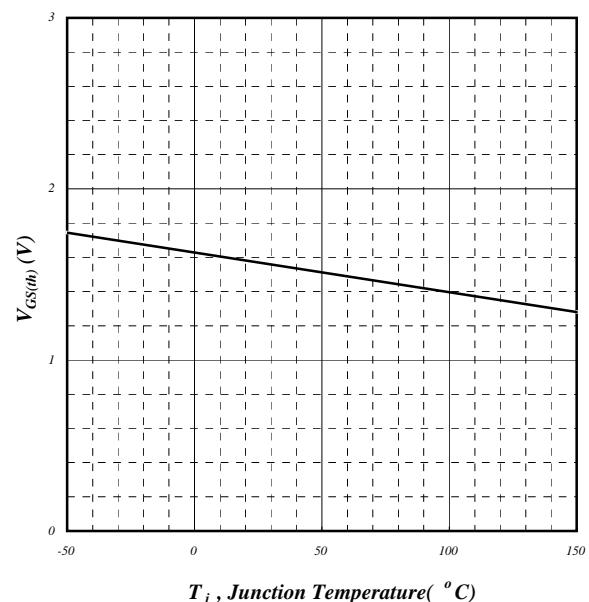


Fig 12. Gate Threshold Voltage v.s. Junction Temperature



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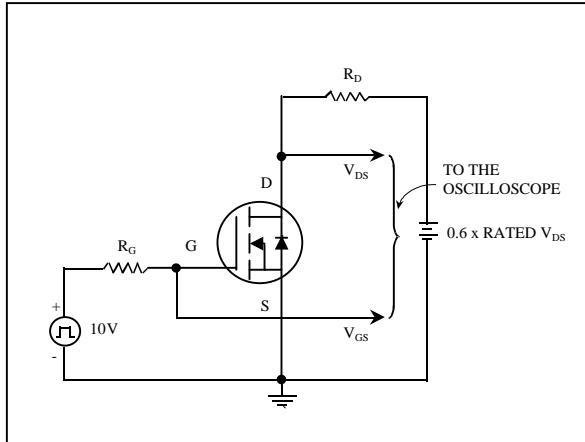


Fig 13. Switching Time Circuit

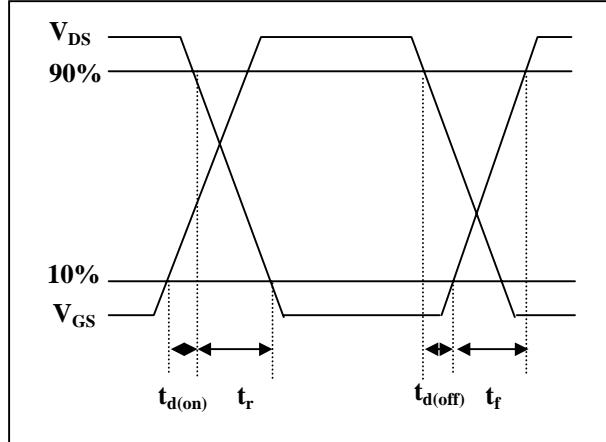


Fig 14. Switching Time Waveform

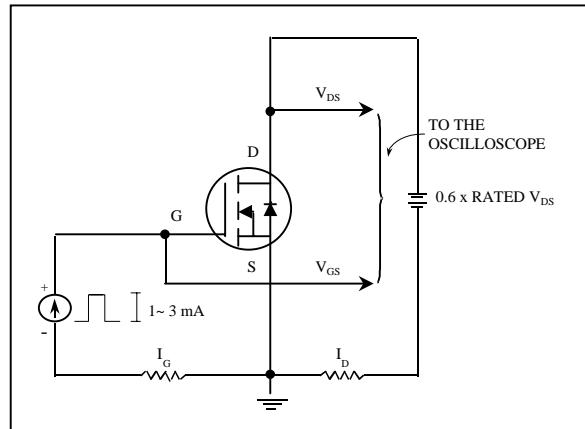


Fig 15. Gate Charge Circuit

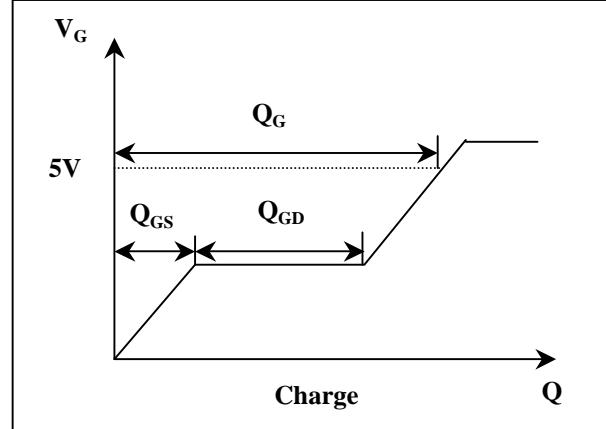


Fig 16. Gate Charge Waveform